

N-channel 650 V, 0.124 Ω typ., 20 A MDmesh™ M2 Power MOSFET in a PowerFLAT™ 8x8 HV package

Datasheet - production data

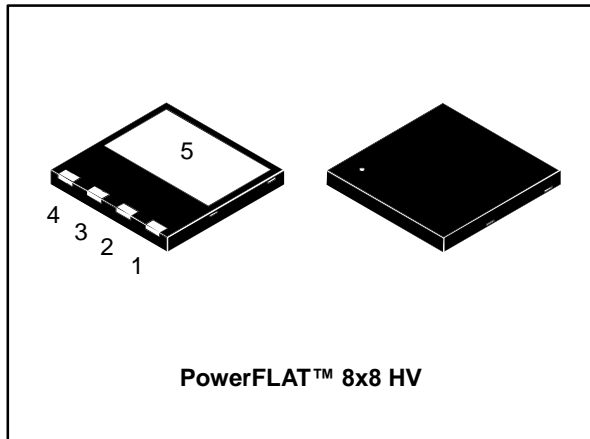
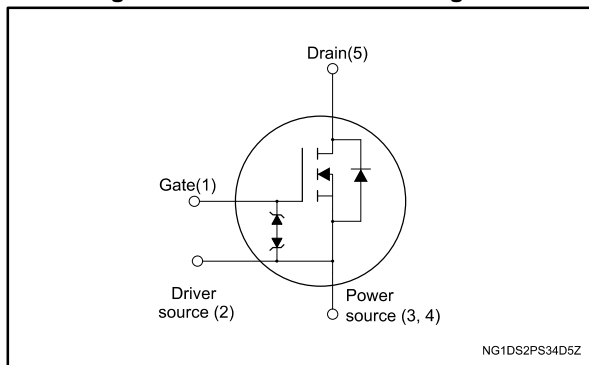


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)max}	I _D
STL33N65M2	650 V	0.154 Ω	20 A

- Extremely low gate charge
- Excellent output capacitance (C_{oss}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Table 1: Device summary

Order code	Marking	Package	Packing
STL33N65M2	33N65M2	PowerFLAT™ 8x8 HV	Tape and reel

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	6
3	Test circuits	8
4	Package information	9
	4.1 PowerFLAT™ 8x8 HV package information.....	10
	4.2 PowerFLAT™ 8x8 HV packing information.....	12
5	Revision history	14

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	20	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	12.6	A
$I_{DM}^{(1)}$	Drain current (pulsed)	80	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	150	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature range	- 55 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		$^\circ\text{C}$

Notes:

(1)Pulse width limited by safe operating area.

(2) $I_{SD} \leq 20\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS(\text{peak})} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$.

(3) $V_{DS} \leq 520\text{ V}$.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.83	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	45	$^\circ\text{C}/\text{W}$

Notes:

(1)When mounted on FR-4 board of inch^2 , 2oz Cu.

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or notrepetitive (pulse width limited by T_{jmax})	2.2	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	600	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$, $T_C = 125\text{ °C}$ ⁽¹⁾			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on- resistance	$V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$		0.124	0.154	Ω

Notes:

⁽¹⁾Defined by design, not subject to production test.

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	1790	-	pF
C_{oss}	Output capacitance		-	75	-	pF
C_{rss}	Reverse transfer capacitance		-	2	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }520\text{ V}$, $V_{GS} = 0$	-	380	-	pF
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 24\text{ A}$ $V_{GS} = 10\text{ V}$ (see Figure 15: "Gate charge test circuit")	-	41.5	-	nC
Q_{gs}	Gate-source charge		-	6.8	-	nC
Q_{gd}	Gate-drain charge		-	18	-	nC

Notes:

⁽¹⁾ $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$, $I_D = 12\text{ A}$ $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 14: "Switching times test circuit for resistive load" and Figure 19: "Switching time waveform")	-	13.5	-	ns
t_r	Voltage rise time		-	11.5	-	ns
$t_{d(off)}$	Turn-off delay time		-	72.5	-	ns
t_f	Current fall time		-	11.5	-	ns

Table 8: Source drain diode

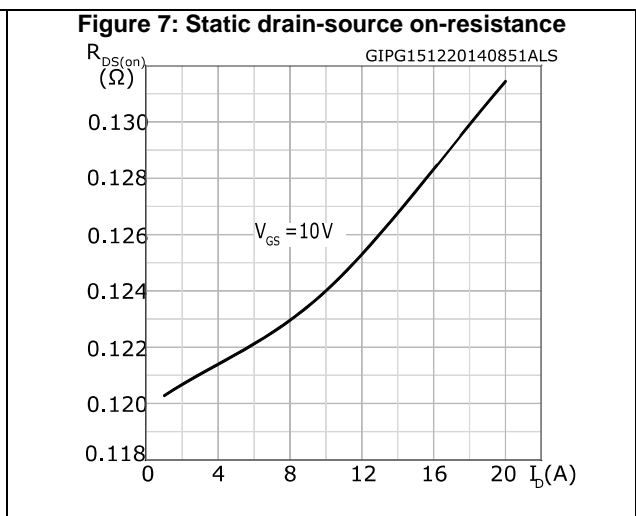
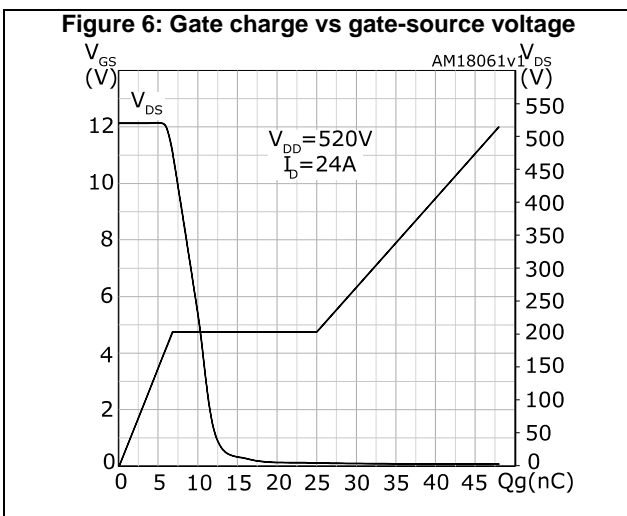
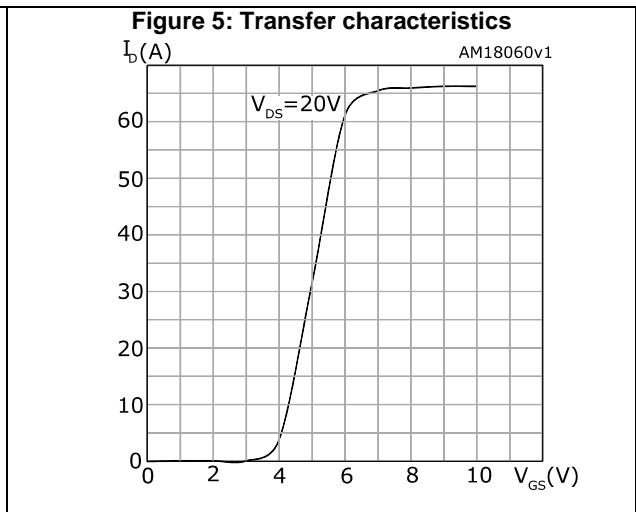
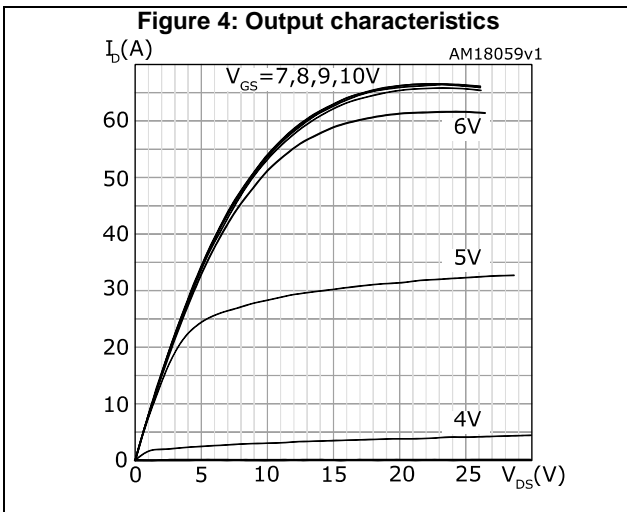
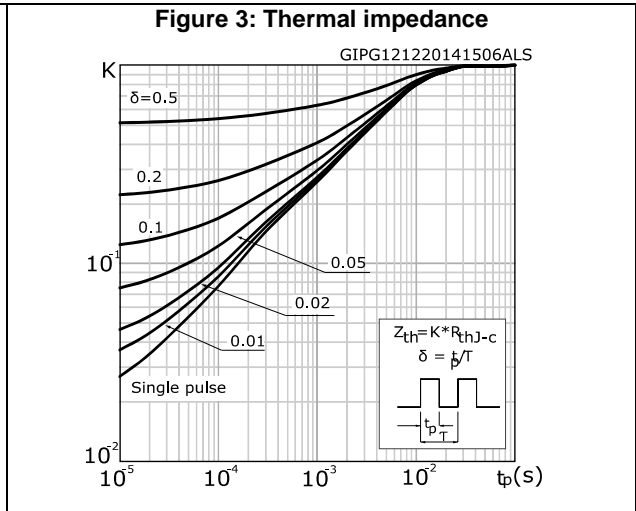
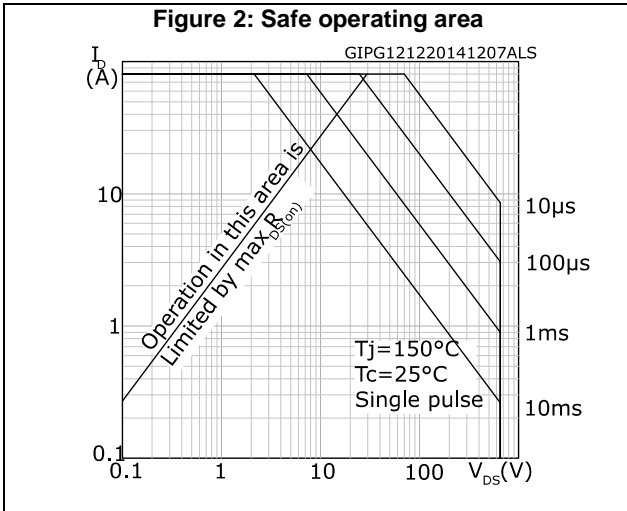
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		20	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		80	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 24\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 24\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 16: "Test circuit for inductive load switching and diode recovery times")	-	426		ns
Q_{rr}	Reverse recovery charge		-	7		μC
I_{RRM}	Reverse recovery current		-	33.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 24\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 16: "Test circuit for inductive load switching and diode recovery times")	-	544		ns
Q_{rr}	Reverse recovery charge		-	10		μC
I_{RRM}	Reverse recovery current		-	36.5		A

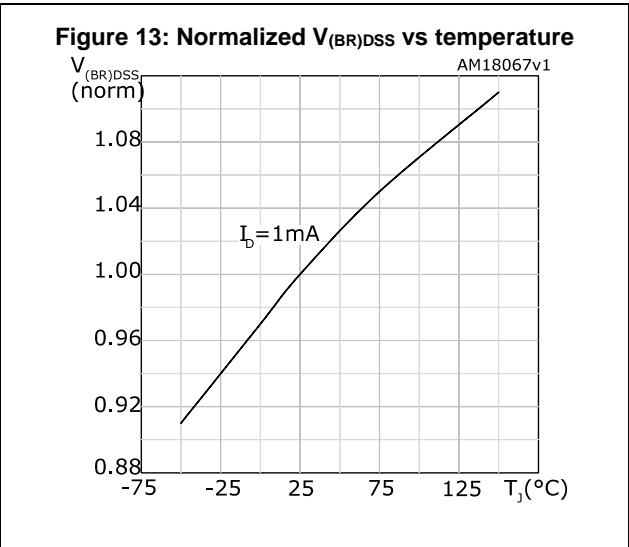
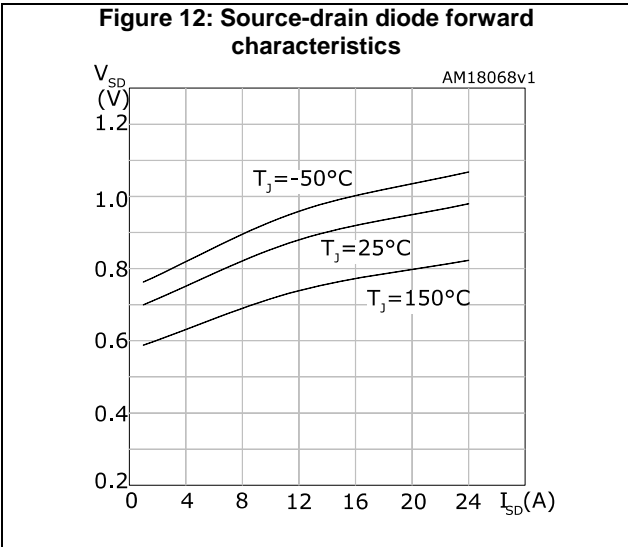
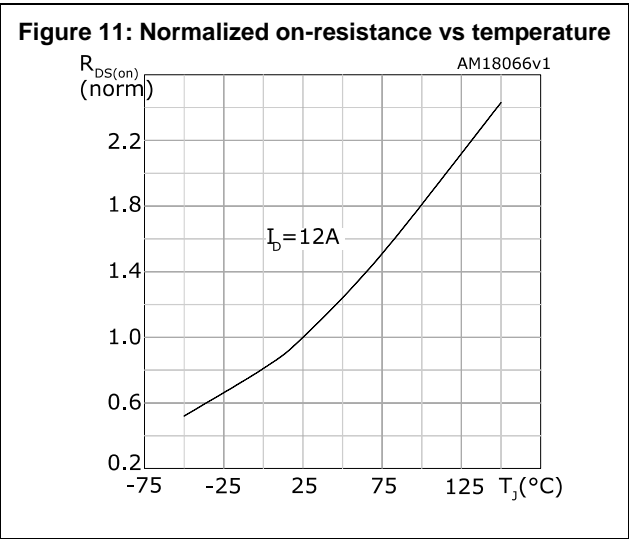
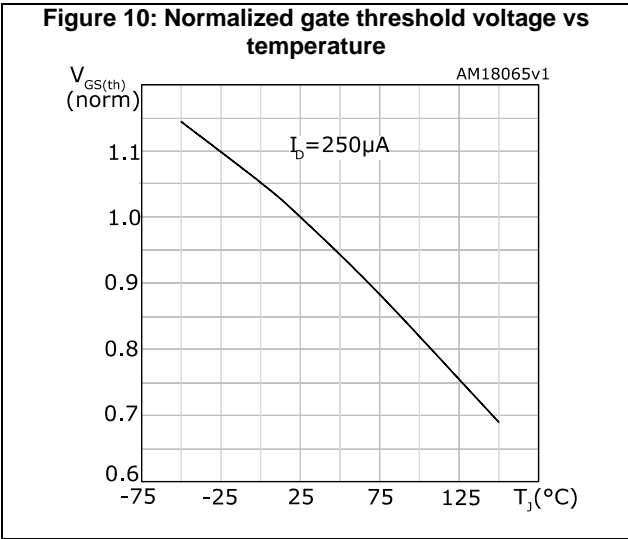
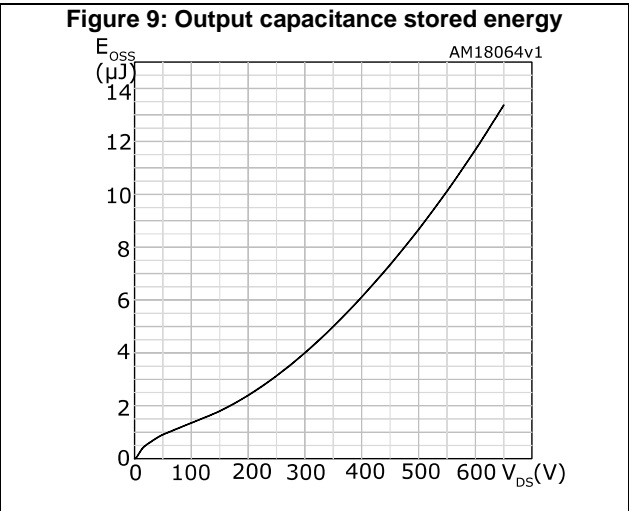
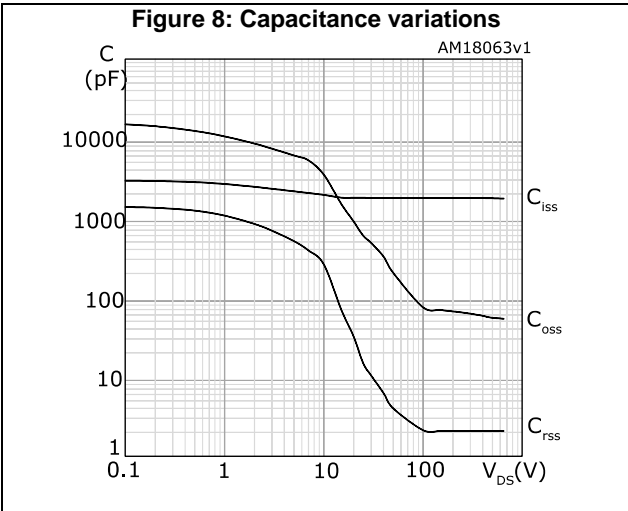
Notes:

(1)Pulse width limited by safe operating area.

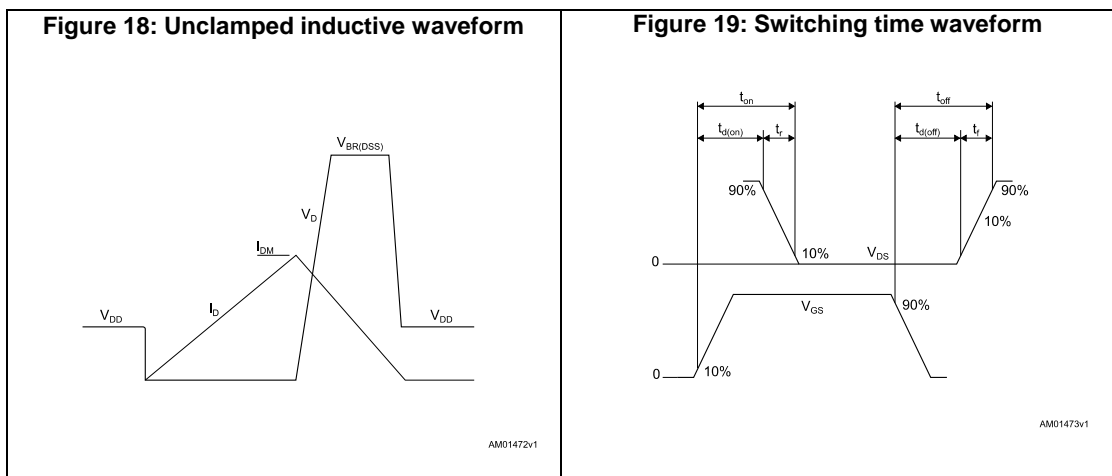
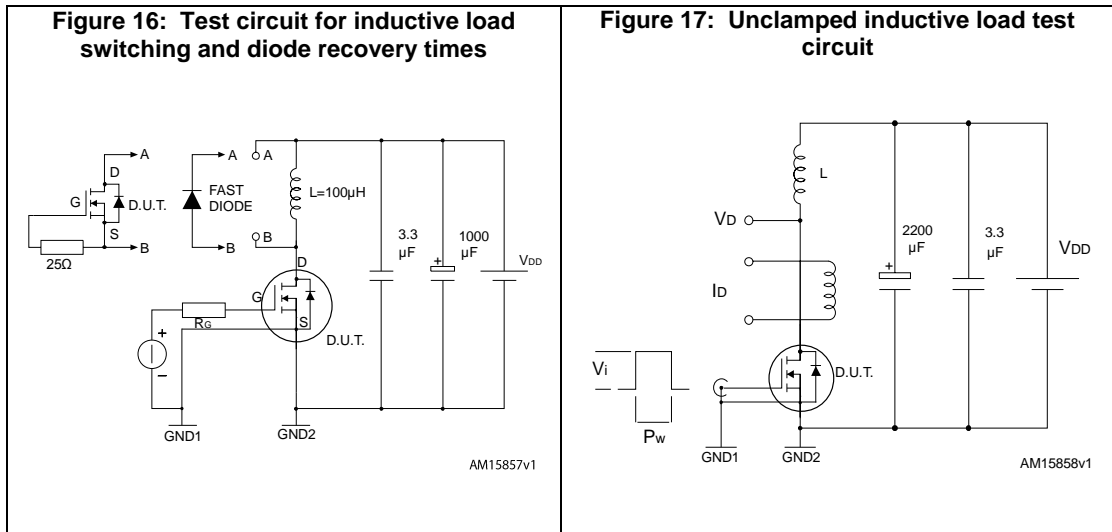
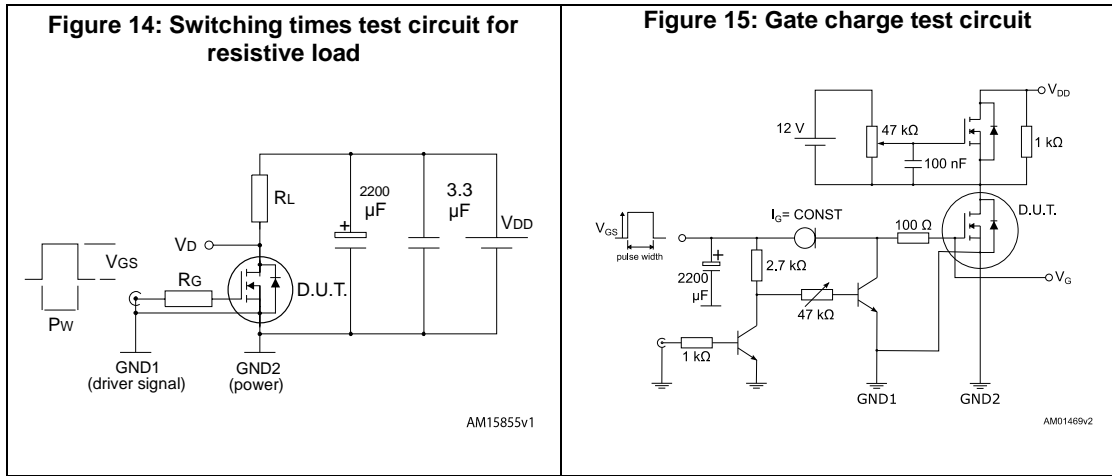
(2)Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)





3 Test circuits



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 PowerFLAT™ 8x8 HV package information

Figure 20: PowerFLAT™ 8x8 HV package outline

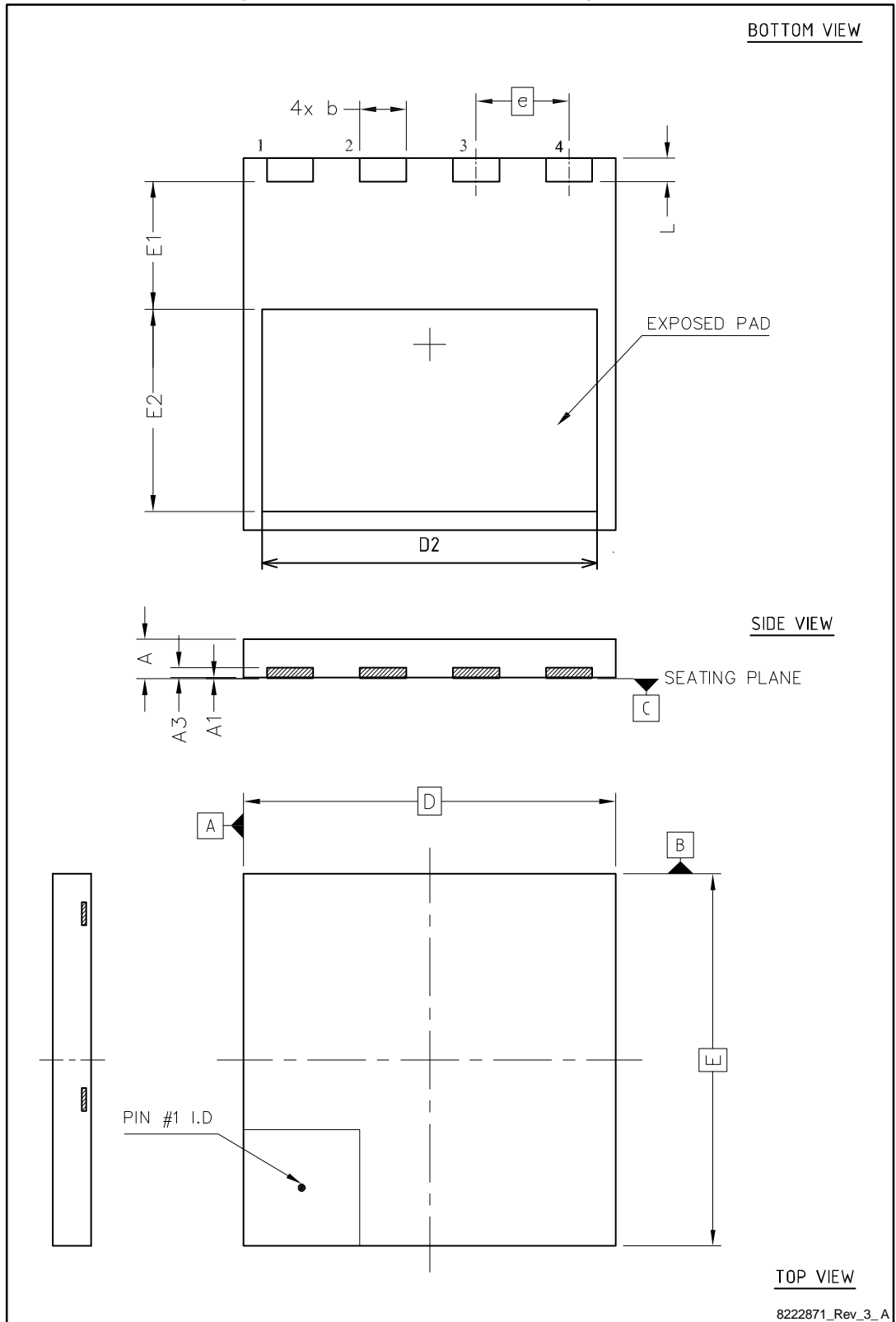
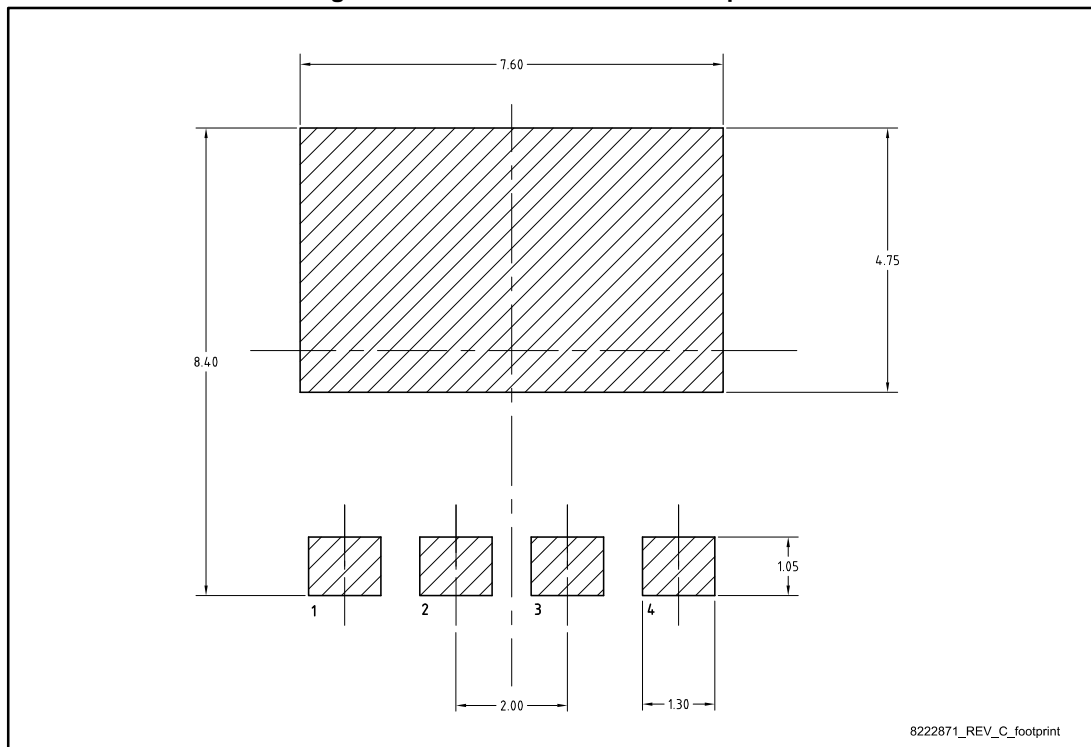


Table 9: PowerFLAT™ 8x8 HV mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.75	0.85	0.95
A1	0.00		0.05
A3	0.10	0.20	0.30
b	0.90	1.00	1.10
D	7.90	8.00	8.10
E	7.90	8.00	8.10
D2	7.10	7.20	7.30
E1	2.65	2.75	2.85
E2	4.25	4.35	4.45
e		2.00	
L	0.40	0.50	0.60

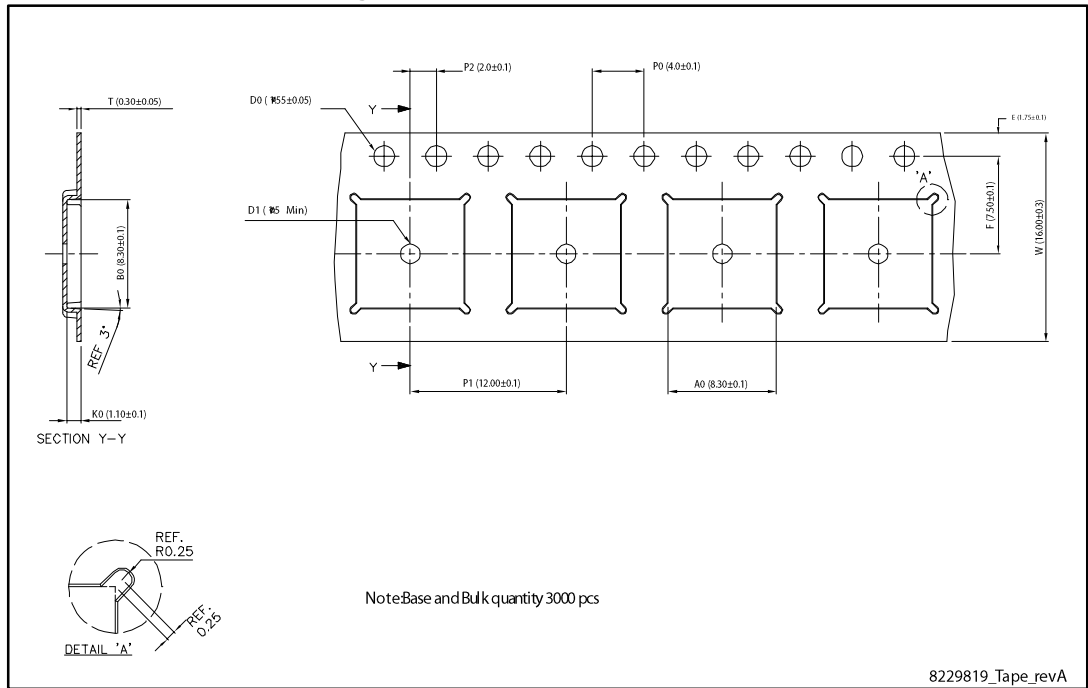
Figure 21: PowerFLAT™ 8x8 HV footprint



All dimensions are in millimeters.

4.2 PowerFLAT™ 8x8 HV packing information

Figure 22: PowerFLAT™ 8x8 HV tape



All dimensions are in millimeters.

Figure 23: PowerFLAT™ 8x8 HV package orientation in carrier tape

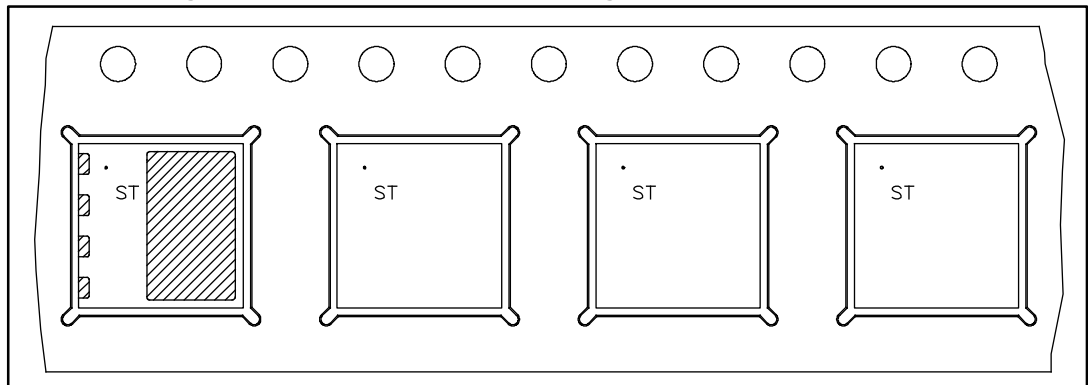
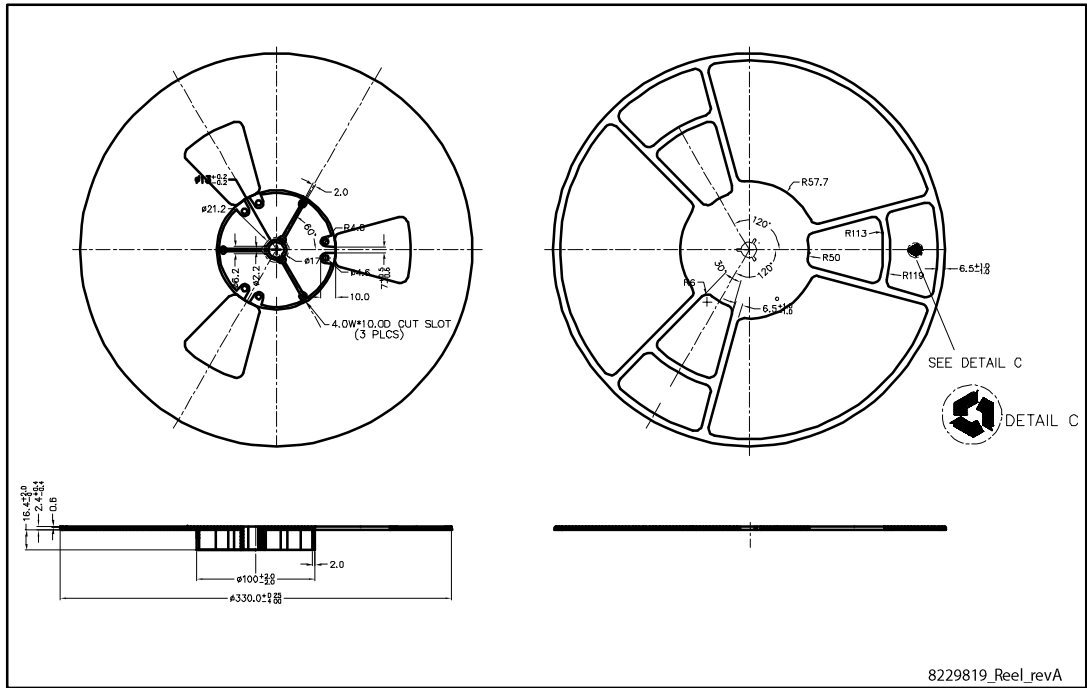


Figure 24: PowerFLAT™ 8x8 HV reel



All dimensions are in millimeters.

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
26-Jun-2013	1	First release.
23-Jul-2014	2	Text edits throughout document. On cover page, updated title, features and description. Updated Table 2: Absolute maximum ratings. Updated Table 3: Thermal data. Added Table 4: Avalanche characteristics. Updated Table 5: On /off states. Updated Table 6: Dynamic. Updated Table 7: Switching times. Updated Table 8: Source drain diode.
13-Apr-2016	3	Updated cover image and <i>Figure 1: "Internal schematic diagram"</i> . Updated <i>Section 3: "Test circuits"</i> . Added footnote in <i>Table 5: "On /off states"</i> . Removed footnote in <i>Table 8: "Source drain diode"</i> . Updated <i>Section 4: "Package information"</i> . Minor text changes.

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